What is claim d is:

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1. A positive photosensitive composition, comprising: a poly(imide-benzoxazole) precursor prepared by the reaction of trimellitic anhydride halide monomer with bis(o-diaminophenol) monomer, wherein the poly(imide-benzoxazole) comprises at least a repeating unit as the structure below:

12 wherein the X is -O- -S-, $-C(CF_3)_2$ -, $-C(CH_3)_2$ -, -13 CO-, $-CH_2$ -, -NHCO-, $-SO_2$ -, -SO-, or a bond; and

n is an integer from 10 to 100;

16 a photosensitizer; and

17 a solvent.

- 2. The positive photosensitive composition as claimed in claim 1, wherein the poly(imide-benzoxazole) precursor is prepared by the reaction of trimellitic anhydride chloride with bis(o-diaminophenol).
- 3. The positive photosensitive composition as claimed in claim 1, wherein the poly(imide-benzoxazole) precursor is prepared by the reaction of trimellitic anhydride chloride with 2, 2-bis(3-amino-4-hydroxyphenol).

- 4. The positive photosensitive composition as claimed in claim 1, wherein X of the poly(imide-benzoxazole) precursor is $-C(CF_3)_2-$.
- 5. The positive photosensitive composition as claimed in claim 1, wherein the poly(imide-benzoxazole) precursor further comprises a repeating unit as the structure below:

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12 13 wherein X is as set forth in claim 1; Ar is

14 wherein Y is -O-, -S-, $-C(CF_3)_2-$, $-C(CH_3)_2-$, -CO-, -

15 CH_2- , $-SO_2-$, or -SO-; and

16 m is an integer and m + n = 10-100.

6. The positive photosensitive composition as claimed in claim 5, wherein the poly(imide-benzoxazole) precursor is prepared by the reaction of trimellitic anhydride chloride monomer, bis(o-diaminophenol) monomer, and terephthalate dichloride monomer.

- 7. The positive photosensitive composition as claimed
- 2 in claim 5, wherein, of the poly(imide-benzoxazole)
- 3 precursor, X is -C(CH₃)₂-, Ar is
- 1 8. The positive photosensitive composition as claimed
- 2 in claim 5, wherein, of the poly(imide-benzoxazole)
- 3 precursor, X is $-C(CH_3)_2-$, Ar is ______
- 9. The positive photosensitive composition—as claimed
- 2 in claim 5, wherein, of the poly(imide-benzoxazole)
- 3 precursor, $m + n = 10 \sim 600$.
- 1 10. The positive photosensitive composition as claimed
- 2 in claim 1, wherein the poly(imide-benzoxazole) precursor is
- 3 20~60 % by weight.
- 1 11. The positive photosensitive composition as claimed
- 2 in claim 10, wherein the poly(imide-benzoxazole) precursor
- 3 is 10~40 % by weight.
- 1 12. The positive photosensitive composition as claimed
- 2 in claim 1, wherein the photosensitizer comprises
- 3 diazonaphthoquinones as the structures of

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6 wherein D is hydrogen,

$$\bigcap_{SO_2}^{O} \bigcap_{SO_2}^{N_2} \bigcap_{OT}^{O} \bigcap_{SO_2}^{O}$$

- 1 13. The positive photosensitive composition as claimed
- 2 in claim 1, wherein the photosensitizer is about 1-80 % by
- 3 weight.

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- 1 14. The positive photosensitive composition as claimed
- 2 in claim 13, wherein the photosensitizer is about 10-40% by
- 3 weight.
- 1 15. The positive photosensitive composition as claimed
- 2 in claim 1, wherein the solvent comprises N-
- 3 methylpyrrolidinone, butyrolactone, N, N-dimethylamide, N,
- 4 N-dimethyl formamide, or mixtures thereof.
- 1 16. The positive photosensitive composition as claimed
- 2 in claim 1, wherein the solvent is about 20-90% by weight.
- 3 17. The positive photosensitive composition as claimed
- 4 in claim 16, wherein the solvent is about 40-80% by weight.
- 1 18. A method of pattern formation, comprising:

2 applying a positive photosensitive composition to form a photoresist layer; 3 performing lithography on the photoresist layer to 4 5 obtain a pattern; and 6 hard baking the substrate to cause dehydrative cyclization of the positive photosensitive 7 8 composition to obtain a final pattern; 9 wherein the positive photosensitive composition comprises: 10 a poly(imide-benzoxazole) precursor prepared by 11 the reaction of trimellitic anhydride halide 12 13 monomer with bis(o-diaminophenol) monomer, 14 wherein poly(imide-benzoxazole) the 15 precursor comprises at least a repeating 16 unit as the structure below: 17 18 19 20 21 22 wherein the X is -O--S-, $-C(CF_3)_2-$, $-C(CH_3)_2-$ 23 , -CO-, -CH₂-, -NHCO-, -SO₂-, -SO-, or a 24 bond; and 25 n is an integer from about 10 to 100; 26 a photosensitizer; and 27 a solvent.

1 19. The method as claimed in claim 18, wherein the 2 poly(imide-benzoxazole) precursor is prepared by the

- 3 reaction of trimellitic anhydride chloride with bis(o-4 diaminophenol).
- 1 20. The method as claimed in claim 18, wherein the
- 2 poly(imide-benzoxazole) precursor is prepared by the
- 3 reaction of trimellitic anhydride chloride with 2, 2-bis(3-
- 4 amino-4-hydroxyphenol).
- 1 21. The method as claimed in claim 18, of the
- 2 poly(imide-benzoxazole) precursor, wherein X is -C(CF₃)₂-.
- 1 22. The method as claimed in claim 18, wherein the
- 2 poly(imide-benzoxazole) precursor further comprises
- 3 repeating unit as the structure below:

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14 wherein Y is -O-, -S-,-C(CF₃)₂-, -C(CH₃)₂-, -CO-, -

15 CH_2- , $-SO_2-$, or -SO-; and

m is an integer and m + n = 10-100.

- 1 23. The method as claimed in claim 22, wherein the
- 2 poly(imide-benzoxazole) precursor is prepared by the
- 3 reaction of trimellitic anhydride chloride monomer, bis(o-
- 4 diaminophenol) monomer, and diacid dichloride monomer.
- 1 24. The method as claimed in claim 22, wherein, of the
- 2 poly(imide-benzoxazole) precursor, X is -C(CH₃)₂-, Ar
- 3 is —
- 1 25. The method as claimed in claim 22, wherein, of the

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- 2 poly(imide-benzoxazole) precursor, X is -C(CH₃)₂-, Ar
- 3 is —
- 1 26. The method as claimed in claim 22, wherein, of the
- 2 poly(imide-benzoxazole) precursor, m + n = 10-600.
- 1 27. The method as claimed in claim 18, wherein the
- 2 poly(imide-benzoxazole) precursor is about 20~60 % by
- 3 weight.
- 1 28. The method as claimed in claim 27, wherein the
- 2 poly(imide-benzoxazole) precursor is about 10~40 % by
- 3 weight.
- 1 29. The method as claimed in claim 18, wherein the
- 2 photosensitizer comprises diazonaphthoquinones as the
- 3 structures of

6 wherein D is hydrogen,

$$\bigcup_{SO_2}^{O} \bigvee_{N_2}^{N_2} \bigvee_{SO_2}^{O} \bigvee_{OT}^{N_2} \bigvee_{SO_2}^{O}$$

- 1 30. The method as claimed in claim 18, wherein the 2 photosensitizer is about 1-80% by weight.
- 31. The method as claimed in claim 30, wherein the photosensitizer is about 10-40% by weight.
- 1 32. The method as claimed in claim 18, wherein the
- solvent comprises N-methylpyrrolidinone, butyrolactone, N,
- 3 N-dimethylamide, N, N-dimethyl formamide, or mixtures
- 4 thereof.

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- 1 33. The method as claimed in claim 18, wherein the
- 2 solvent is about 20-90% by weight.

- 3 34. The method as claimed in claim 33, wherein the solvent is about 40-80% by weight.
- 35. The method as claimed in claim 18, wherein the lithography comprises:
- 3 pre-baking the substrate with a photoresist layer
 4 thereon;
- 5 exposing the substrate uisng a mask under a light 6 source to obtain a exposure region; and
- eliminating the exposure region by a hydrophilic developer to obtain a pattern.
- 1 36. The method as claimed in claim 35, wherein the
- 2 light source is X-ray, electron beam, ultraviolet light, or
- 3 visible light.
- 4 37. The method as claimed in claim 35, wherein the
- 5 hydrophilic developer comprises alkali, primary amine,
- 6 secondary amine, tertiary amine, aminoalcohol, quaternary
- 7 amine salt, or mixtures thereof.